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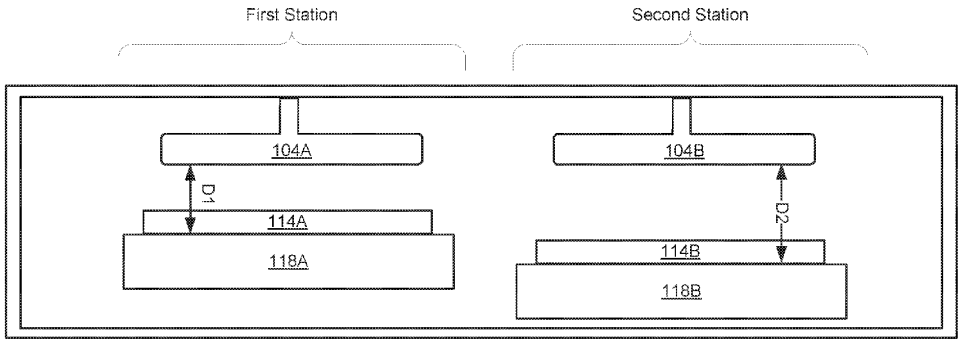


Figure 7

(57) Abstract: Methods and apparatuses for depositing material onto substrates in a multi-station deposition apparatus having a first station and a second station are provided. One method may include providing a first substrate onto a first pedestal of the first station, providing a second substrate onto a second pedestal of the second station, and for a first part of a deposition process, simultaneously generating a first plasma at the first station while the first pedestal is separated by a first distance from a first showerhead of the first station, thereby depositing a first layer of material onto the first substrate, and a second plasma at the second station while the second pedestal is separated by a second distance from a second showerhead of the second station, thereby depositing a second layer of material onto the second substrate, in which the first distance is different than the second distance.

WO 2020/185539 A1

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